

DUAL P-CHANNEL ENHANCEMENT MODE FIELD EFFECT TRANSISTOR
Product Summary

BV _{DSS}	R _{DS(ON)} max	I _D T _A = +25°C
-30V	45mΩ @ V _{GS} = -10V	-6.9A
	65mΩ @ V _{GS} = -4.5V	-5.1A

Description

This new generation MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

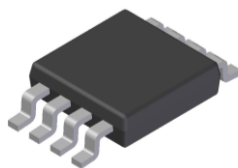
- Power Management Functions
- Backlighting
- DC-DC Converters

Features

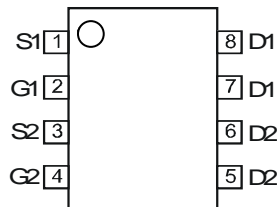
- Dual P-Channel MOSFET
- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**
- **PPAP Capable (Note 4)**

Mechanical Data

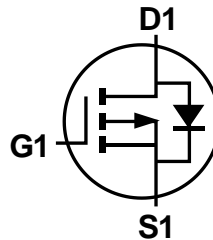
- Case: SO-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish - Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208e3
- Weight: 0.072g (Approximate)



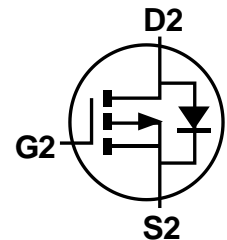
Top View


 Top View
Internal Schematic

SO-8



P-Channel MOSFET

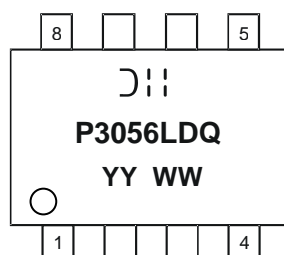


P-Channel MOSFET

Ordering Information (Note 5)

Part Number	Case	Packaging
DMP3056LSDQ-13	SO-8	2,500/Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to <https://www.diodes.com/quality/product-compliance-definitions/>.
 5. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

Marking Information


DII = Manufacturer's Marking
 P3056LDQ = Product Type Marking Code
 YYWW = Date Code Marking
 YY = Year (ex: 17 = 2017)
 WW = Week (01 to 53)

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Drain-Source Voltage	V _{DSS}	-30	V
Gate-Source Voltage	V _{GSS}	±20	V
Drain Current (Note 6)	I _D	T _A = +25°C	-6.9
Steady State		T _A = +70°C	-5.8
Pulsed Drain Current (Note 7)	I _{DM}	-24	A

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 6)	P _D	2.5	W
Thermal Resistance, Junction to Ambient (Note 6)	R _{θJA}	50	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						
Drain-Source Breakdown Voltage	BV _{DSS}	-30	—	—	V	V _{GS} = 0V, I _D = -250μA
Zero Gate Voltage Drain Current	I _{DSS}	—	—	-1	μA	V _{DS} = -30V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	±100 ±800	nA	V _{GS} = ±20V, V _{DS} = 0V V _{GS} = ±25V, V _{DS} = 0V
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	V _{GS(TH)}	-1	-1.7	-2.1	V	V _{DS} = V _{GS} , I _D = -250μA
Static Drain-Source On-Resistance	R _{DS(ON)}	—	—	45 65	mΩ	V _{GS} = -10V, I _D = -6.0A V _{GS} = -4.5V, I _D = -5.0A
Forward Transconductance	g _{fs}	—	8	—	S	V _{DS} = -10V, I _D = -5.3A
Diode Forward Voltage (Note 8)	V _{SD}	-0.5	—	-1.2	V	V _{GS} = 0V, I _S = -1.7A
DYNAMIC CHARACTERISTICS						
Input Capacitance	C _{iSS}	—	722	—	pF	V _{DS} = -25V, V _{GS} = 0V f = 1.0MHz
Output Capacitance	C _{oss}	—	114	—	pF	
Reverse Transfer Capacitance	C _{rSS}	—	92	—	pF	
Gate Resistance	R _G	—	3.3	—	Ω	V _{DS} = 0V, V _{GS} = 0V f = 1.0MHz
SWITCHING CHARACTERISTICS						
Total Gate Charge	Q _G	—	6.8	—	nC	V _{DS} = -15V, V _{GS} = -4.5V, I _D = -6A
	Q _G	—	13.7	—	nC	
Gate-Source Charge	Q _{GS}	—	1.6	—	nC	V _{DS} = -15V, V _{GS} = -10V, I _D = -6A
Gate-Drain Charge	Q _{GD}	—	4.2	—	nC	
Turn-On Delay Time	t _{D(ON)}	—	6.4	—	ns	V _{DS} = -15V, V _{GS} = -10V, I _D = -1A, R _G = 6.0Ω
Rise Time	t _R	—	5.3	—		
Turn-Off Delay Time	t _{D(OFF)}	—	26.5	—		
Fall Time	t _F	—	14.7	—		

- Notes:
- Device mounted on 2 oz. 1" x 1" Copper pads on 2" x 2" FR-4 PCB.
 - Pulse width ≤10μs, Duty Cycle ≤1%.
 - Short duration pulse test used to minimize self-heating effect.

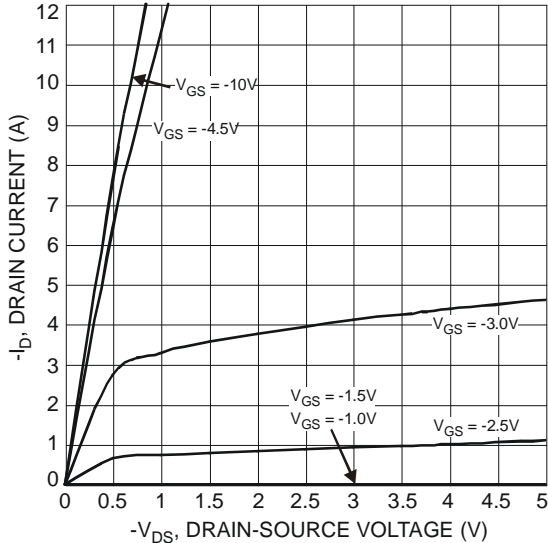


Fig. 1 Typical Output Characteristics

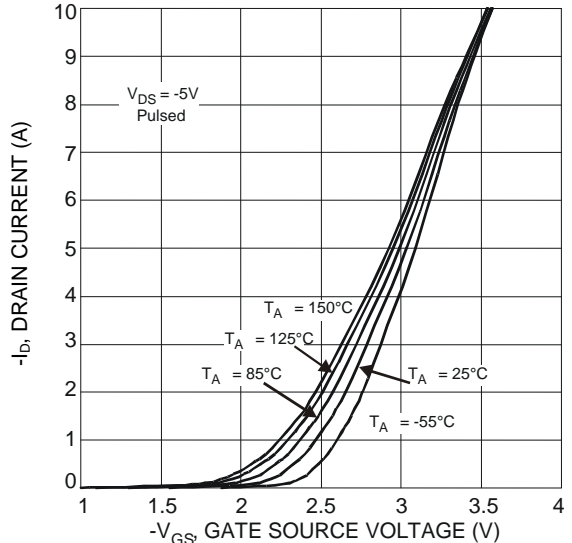


Fig. 2 Typical Transfer Characteristics

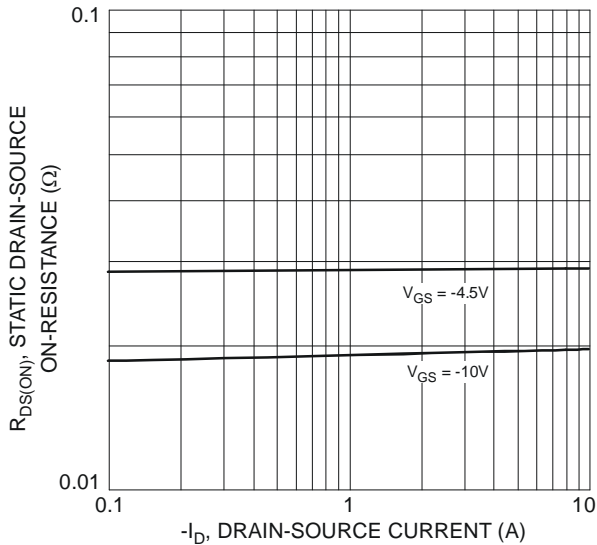


Fig. 3 On-Resistance vs. Drain Current & Gate Voltage

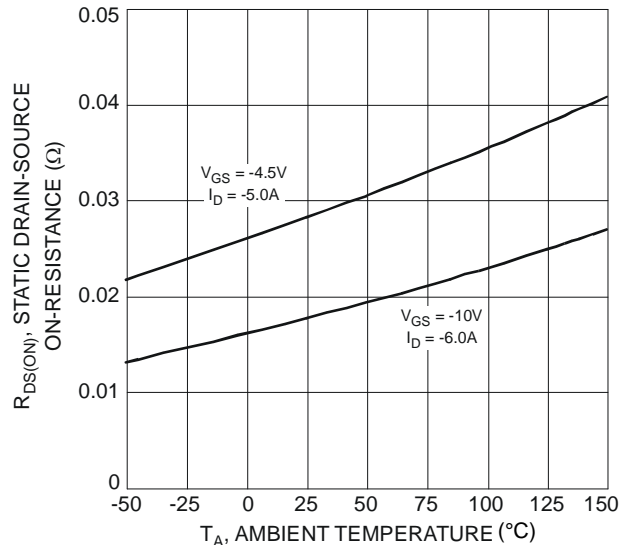


Fig. 4 Static Drain-Source On-Resistance vs. Ambient Temperature

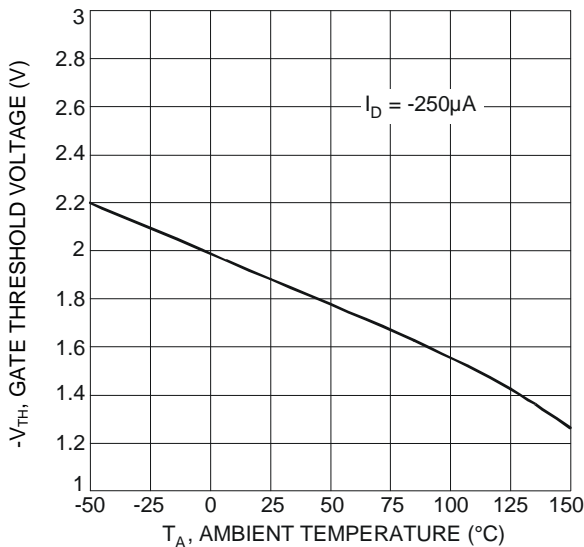


Fig. 5 Gate Threshold Variation vs. Ambient Temperature

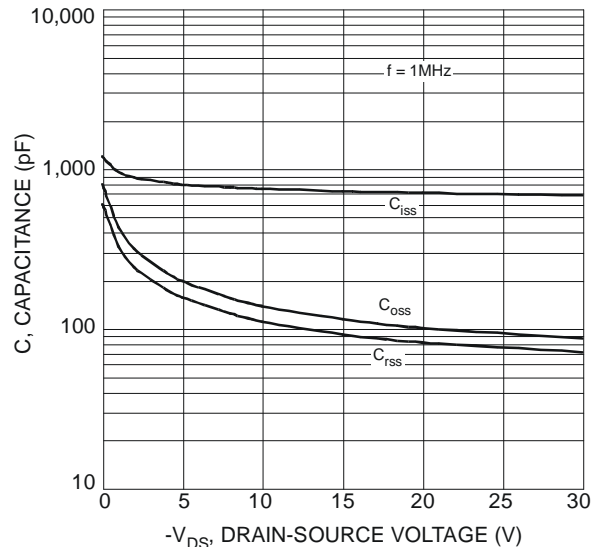


Fig. 6 Typical Total Capacitance

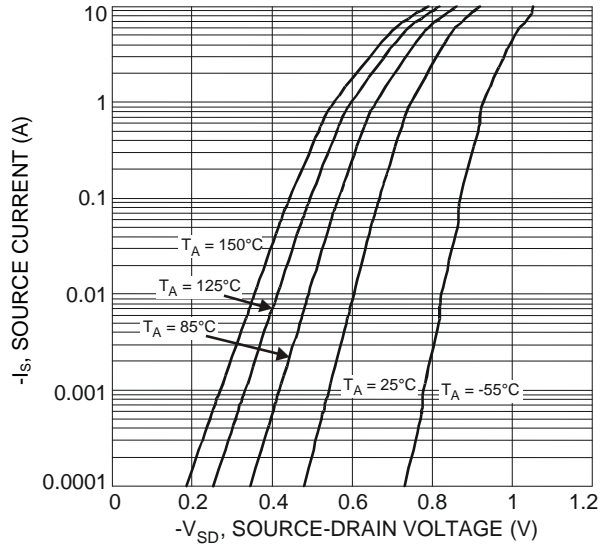
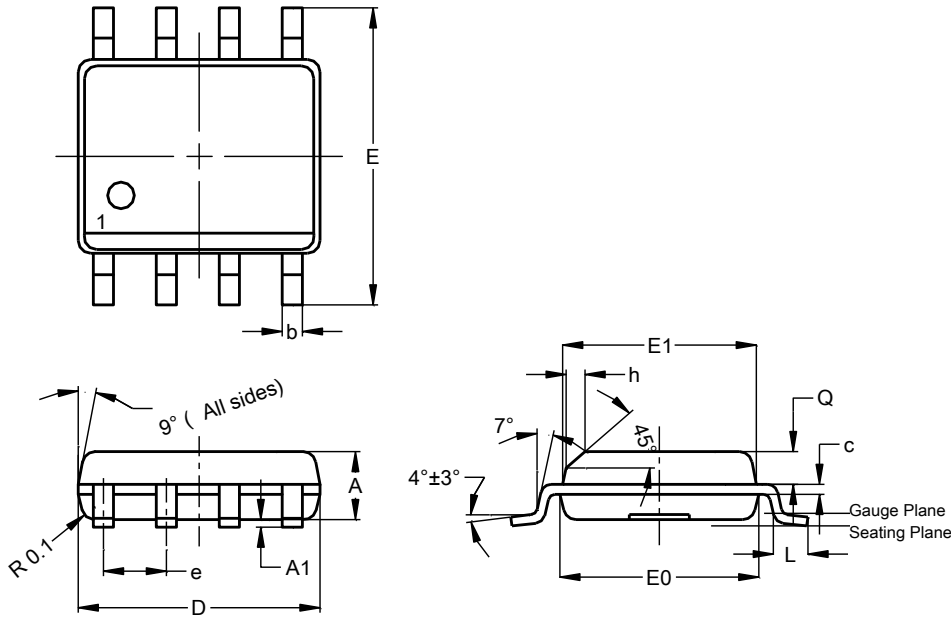


Fig. 7 Source Current vs. Source-Drain Voltage

Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

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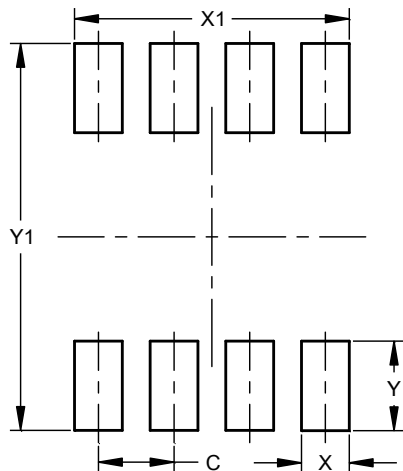


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Dim	Min	Max	Typ
A	1.40	1.50	1.45
A1	0.10	0.20	0.15
b	0.30	0.50	0.40
c	0.15	0.25	0.20
D	4.85	4.95	4.90
E	5.90	6.10	6.00
E1	3.80	3.90	3.85
E0	3.85	3.95	3.90
e	--	--	1.27
h	-	--	0.35
L	0.62	0.82	0.72
Q	0.60	0.70	0.65
All Dimensions in mm			

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

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Dimensions	Value (in mm)
C	1.27
X	0.802
X1	4.612
Y	1.505
Y1	6.50

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